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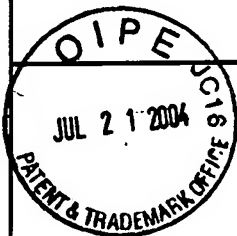
TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
3816.06-C1

In Re Application Of: **Raanan Y. ZEHAVI et al.**

Application No.	Filing Date	Examiner	Customer No.	Group Art Unit	Confirmation No.
10/829,641	04/22/04	unknown	22337	2818	6952

Title: **SILICON FIXTURE SUPPORTING SILICON WAFERS DURING HIGH TEMPERTURE PROCESSING**



Address to:

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

37 CFR 1.97(b)

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:
- ☐ the statement specified in 37 CFR 1.97(e);
- OR**
- ☐ the fee set forth in 37 CFR 1.17(p).

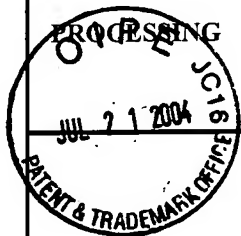
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SILICON FIXTURE SUPPORTING SILICON WAFERS DURING HIGH TEMPERTURE



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(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

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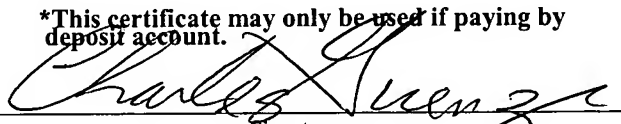
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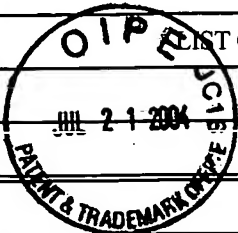
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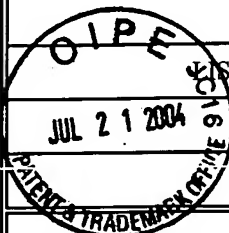
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Dated: **July 19, 2004**

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U.S. Department of Commerce, Patent and Trademark Office					Docket No.: 3816.06-C1			
					Serial No.: 10/829,641			
					Applicant: Ranaan ZEHAVI et al.			
(Use several sheets if necessary)					Filing Date: April 22, 2004			
					Group: 2818			
U.S. PATENT DOCUMENTS								
*Examiner Initial	AA	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA	5,492,229	02/2096	Tanaka et al.	211	41.18		
	AB	5,516,283	05/14/96	Schrems	432	241		
	AC	5,534,074	07/09/96	Koons	118	728		
	AD	5,586,880	12/24/96	Ohsawa	432	241		
	AE	5,595,604	01/21/97	Kobayashi et al.	118	715		
	AF	5,752,609	05/19/98	Kato et al.	211	41.18		
	AH	5,779,797	07/14/98	Kitano et al.	118	500		
	AI	5,858,103	01/12/99	Nakajima et al.	118	728		
	AJ	5,931,666	08/03/99	Hengest	432	258		
FOREIGN PATENT DOCUMENTS (Translation)								
		Document Number	Date	Country	Class	Subclass	Yes	No
	AL	WO 00/21119	04/13/00	PCT			X	
	AM	EP 0 884 769 A 1	12/16/98	Europe			X	
	AN							
	AO							
	AP							
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
	AR	anonymous, "Epi-II advanced Wafer," <i>MEMC Applications Note</i> , AE-003, March 2000, pp. 1-4						
	AS	anonymous, "Thin epi layers shown to improve gate oxide integrity performance," MEMC, date unknown, 1.p						
	AT							
Examiner			Date Considered					
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.								

U.S. Department of Commerce, Patent and Trademark Office					Docket No.: 3816.06-C1			
 LIST OF RELEVANT ART CITED BY APPLICANT (Use several sheets if necessary)					Serial No.: 10/829,641			
					Applicant: Raanan Y. ZEHAVI et al.			
					Filing Date: April 22, 2004			
					Group: 2818			
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA	6,065,615	05/23/00	Uchiyama et al.	211	41.18		
	AB	6,171,982	01/09/01	Sato	438	795		
	AC	6,180,497	01/30/01	Sato et al.	438	458		
	AD	6,284,997	09/04/01	Zehavi et al.	219	121.46		
	AE	6,450,346	09/17/02	Boyle et al.	219	41.18		
	AF	6,727,191	04/27/04	Zehavi et al.	438	795	12/23/98	
	AG							
	AH							
FOREIGN PATENT DOCUMENTS (Translation)								
		Document Number	Date	Country	Class	Subclass	Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							
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	AS							
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Examiner			Date Considered					
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